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A polishing system, comprising:

a polishing pad; and

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a spray element adapted to spray a pressurized fluid upon the polishing pad to remove matter adhered to the pad, wherein said matter is adhered to the polishing pad during a polishing process of a semiconductor topography.

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2. The system of claim 1, further comprising a dispense component adapted to dispense a polishing fluid onto the polishing pad during said polishing process.

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The system of claim 2, wherein said matter comprises particles from the polishing fluid.

4. The system of claim 1, wherein said matter comprises particles from the semiconductor topography.

5. The system of claim 1, adapted to allow the pressurized fluid to be dispensed across the entirety of the polishing pad.

6. The system of claim 1, wherein the spray element is positioned across at least half of the width of the polishing pad.

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- 7. The system of claim 6, wherein the polishing pad comprises a circular pad and the spray element extends across the radius of the polishing pad.
- 8. The system of claim 6, wherein the polishing pad comprises a belt and the spray element extends across the width of the belt.

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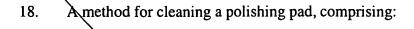
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- 9. The system of claim 1, wherein said polishing pad comprises a plurality of pores, and wherein a portion of the matter is embedded within one or more of the pores.
- 5 10. The system of claim 1, wherein the spray element is adapted to be removed from the system.
- 11. A spray element adapted to be positioned within a polishing system, wherein the spray element is further adapted to remove matter adhered to a polishing pad of the system by spraying a pressurized fluid upon the polishing pad.
  - 12. The spray bar of claim 11, wherein the spray element is adapted to be positioned within the polishing system such that the pressurized fluid is dispersed across a region extending across at least half of the width of the polishing pad.
  - 13. The spray bar of claim 11, comprising a plurality of nozzles arranged such that the nozzles are projected toward the polishing pad upon positioning the spray element to the system.
  - The spray bar of claim 13, wherein a spray distribution from one of said plurality nozzles overlaps a spray distribution from an adjacent nozzle.
    - 15. The spray ban of claim 13, further comprising shields arranged about the plurality of nozzles.
    - 16. The spray bar of claim 15, wherein said shields are arranged along the sides of the years element parallel to the projection of the nozzles.
    - 17. The spray bar of claim 11, comprising a mounting structure with which to couple the spray element to the polishing system.

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moving the polishing pad relative to a spray element, wherein the spray element and polishing pad are positioned within a polishing system such that fluid openings of the spray element are positioned toward the polishing pad;

spraying a pressurized fluid from the spray element upon the polishing pad during said moving; and

removing matter adhered to the polishing pad.

19. The method of claim 18, wherein said spraying is conducted after polishing one or more semiconductor topographies with the polishing system.

20. The method of claim 18, wherein the duration of said spraying is sufficient such that the pressurized fluid is dispensed across the entire upper surface of the polishing pad.

- 21. The method of claim 18, wherein said spraying comprises spraying the fluid at asufficient pressure to dislodge the matter adhered to the polishing pad.
  - 22. The method of claim 18, wherein said spraying comprises spraying the fluid at a pressure between approximately 25 psi and approximately 45 psi.

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A method for polishing multiple semiconductor topographies, comprising:

moving a polishing pad with respect to a semiconductor topography and a spray element;

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polishing the semiconductor topography by positioning it against the moving polishing pad;

spraying a pressurized fluid from the spray element upon the polishing pad while continuing to move the polishing pad; and

removing matter adhered to the polishing pad.

24. The method of claim 23, further comprising:

polishing one or more additional topographies; and

repeating said spraying and removing after said polishing one or more additional topographies.

The method of clasm 23, wherein said spraying is conducted at a predetermined 25. time.

The method of claim 23, wherein said spraying is conducted after said polishing. 26.

27. The method of claim 23, wherein said spraying and said polishing are conducted

28. The method of claim 23, further comprising applying a polishing fluid from a dispense component prior to said polishing.